1 Supplementary Information

2 Elastic strain-induced amorphization in high-entropy alloys

- 3 Yeqiang Bu^{1,2#}, Yuan Wu^{3,4#*}, Zhifeng Lei⁵, Xiaoyuan Yuan³, Leqing Liu³, Peng Wang⁶, Xiongjun Liu³,
- 4 Honghui Wu³, Jiabin Liu^{1,7*}, Hongtao Wang^{1,2*}, R. O. Ritchie⁸, Zhaoping Lu^{3*}, Wei Yang¹
- ¹Center for X-mechanics, School of Aeronautics and Astronautics, Zhejiang University, Hangzhou
 310027, China
- ²ZJU-Hangzhou Global Scientific and Technological Innovation Center, Zhejiang University, Hangzhou
 310027, China
- 9 ³Beijing Advanced Innovation Center for Materials Genome Engineering, State Key Laboratory for
- 10 Advanced Metals and Materials, University of Science and Technology Beijing, Beijing 100083, China
- ⁴ Institute for Materials Intelligent Technology, Liaoning Academy of Materials, Shenyang, 110010,
 China
- 13 ⁵College of Materials Science and Engineering, Hunan University, Changsha 410082, China
- 14 ⁶Shanghai Key Laboratory of Mechanics in Energy Engineering, Shanghai Institute of Applied
- 15 Mathematics and Mechanics, School of Mechanics and Engineering Science, Shanghai University,
- 16 Shanghai 200444, China
- 17⁷ State Key Laboratory of Silicon and Advanced Semiconductor Materials, School of Materials Science
- 18 and Engineering, Zhejiang University, Hangzhou 310027, China
- 19 ⁸Department of Materials Science and Engineering, University of California, Berkeley, CA 94720, USA
- 20 *#These authors contributed equally to the work.*
- 21 To whom correspondence should be addressed. E-mails: <u>wuyuan@ustb.edu.cn</u> (Yuan Wu),
- 22 <u>liujiabin@zju.edu.cn</u> (Jiabin Liu), <u>htw@zju.edu.cn</u> (Hongtao Wang) and <u>luzp@ustb.edu.cn</u> (Zhaoping
- 23 *Lu*)

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Supplementary discussion 1

2 1. Evaluation for the effects of electron irradiation

3 It should be noted that electron irradiation may also artificially induce amorphization. Here, the effects of electron irradiation were fully evaluated through 4 "knock on" and "heating" effects ^{1,2}. To evaluate the "knock-on" effects of electron 5 irradiation on the nanoscale HEA samples, we exposed a nanoscale TiHfZrNb sample 6 7 to an electron beam for 30 minutes. Subsequent examination of this sample revealed that the shape and location of crystal-amorphous interface, crystal orientation and 8 lattice spacing in the TEM pictures and the corresponding FTT image (Fig. S3) 9 10 remained unchanged after irradiation, indicating that the incident beam did not cause a 11 "knock on" effect during this exposure period. As for any "heating" effect, a theoretical estimate on the temperature rise induced by electron irradiation is shown in following 12 formulas ^{3,4}: 13

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$$\Delta T = \frac{I}{4\pi K e} \left(\frac{\Delta E}{d}\right) (1 + 2\ln\frac{b}{r_0}) \tag{1}$$

$$-\frac{\Delta E}{d} = \frac{2\pi Z \rho (e^2 / 4\pi \varepsilon_0)^2}{mv^2} \left\{ \ln \left[\frac{E(E+mc^2)^2 \beta^2}{2I_e^2 mc^2} \right] + (1-\beta^2) - (1-\sqrt{1-\beta^2}+\beta^2) \ln 2 + \frac{1}{8} (1-\sqrt{1-\beta^2})^2 \right\}$$
16 (2)

where K is the thermal conductivity of the sample, I is the beam current, ΔE is the total 17 energy loss per electron in a sample of thickness d, b is the radius of the heat sink, and 18 19 r_0 is the beam radius, Z is the atomic number of the samples, ρ is the atomic density, ε_0 is the vacuum dielectric constant, *m* is the electron rest mass, *v* is the electron velocity, 20 21 c is the speed of light, E is the electron energy, I_e is the average excitation energy of electrons in the target, and $\beta = v/c$. Given K = 7.955 W(m·K)⁻¹, I = 3 nA, b = 1.5 mm, 22 $\rho = 2.58 \times 10^{28} \text{ m}^{-3}$, $r_0 = 200 \text{ nm}$, Z = 43.75, $e = 1.6 \times 10^{-19} \text{ C}$, $\varepsilon_0 = 8.85 \times 10^{-12} \text{ F} \cdot \text{m}^{-1}$, m 23 $= 9.3 \times 10^{-31}$ kg, $v = 2.0837 \times 10^8$ m·s⁻¹, $c = 3.0 \times 10^8$ m·s⁻¹, E = 200 keV, $I_e = 385$ eV, 24 we calculated the temperature rise (ΔT) to be 0.45 K, which can be neglected. However, 25 it is possible that other artificial effects could be caused by the synergy of the electron 26

- 1 beam and applied stress. Comparing the pre- and post-mortem high-resolution images,
- 2 strain-induced amorphization is still observed in the TiHfZrNb sample stretched in the
- 3 beam blank condition (Fig. S4). Accordingly we conclude that the effects of electron
- 4 irradiation on the deformation behavior of the samples can be neglected.

1 2. Elastic instability via dislocation-related behaviors in bulk TiHfZrNb

The post-mortem microstructure characterization of bulk TiHfZrNb samples after tensile test has been closely performed in our previous work ⁵. The TEM and XRD results show that dislocation slip mediates the deformation of bulk TiHfZrNb, while elastic strain-induced amorphization is absent. The *in situ* TEM tensile test of the TiHfZrNb foil with submicron thickness has also been performed in our previous work ⁵, where extensive dislocation nucleation and propagation were observed.

We investigated the post-mortem microstructure of the bulk TiHfZrNb samples 8 heavily cool-rolled with a reduction ratio of 90%. Several band-like structures were 9 10 observed, as shown in Fig. S6a. Figure S6b is the corresponding SAED pattern, where 11 a diffuse diffraction ring can be clearly recognized, indicating occurrence of the localized amorphization in those bands. Such localized amorphization event was further 12 confirmed by high-resolution TEM images (Figs. S6c and d). Nevertheless, it is critical 13 to point out that the formation mechanism of those amorphous bands is totally different 14 from that in our nanoscale samples. We carefully characterized the microstructure of 15 the 30% rolled bulk TiHfZrNb alloy, as shown in Fig. S7, where only a high density of 16 dislocations was observed without any sign of amorphous structure. Therefore, the low 17 elastic strain limit of bulk alloys (usually less than 1%) would lead to the prevalent 18 19 dislocation generation and the resultant defect accumulation amorphization, similar to what had been reported in extremely deformed bulk CrMnFeCoNi HEAs ⁶. Such defect 20 accumulation process inhibits the elastic strain-induced amorphization in bulk 21 22 TiHfZrNb HEA, resulting in a completely different responses to external stress.

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3. Energy landscape of elastic strain-induced amorphization

The energy landscape of elastic strain-induced amorphization is studied using First 2 3 Principles (Density Functional Theory) simulations. The energy of the amorphous and crystalline structures, as well as the system energy evolution of TiHfZrNb with elastic 4 5 strain, was calculated. The amorphous configuration was obtained by quenching the liquid TiHfZrNb from 3000 K to 0 K at an infinite cooling rate (Fig. S13a). The energy 6 of the amorphous TiHfZrNb was calculated as -8.981 eV atom⁻¹. The energy of the 7 relaxed atomic configuration of crystalline TiHfZrNb (Fig. S13b) was calculated as -8 9.037 eV atom⁻¹, which is lower than that of the amorphous state. As elastic strain 9 increases, the energy of the TiHfZrNb lattice gradually increases (Fig. S13d) and 10 reaches -8.975 eV atom⁻¹ at an elastic strain of 10% (Fig. S13c), which exceeds that of 11 the amorphous state and indicates that the highly tension-loaded samples are unstable 12 compared to the amorphous state. These results suggest that the energy barrier between 13 14 the crystal and its amorphous counterpart can be overcome by storing elastic strain 15 energy through a large elastic strain (~10%).

Supplementary Table 1. The elastic instability mechanisms of alloys with various number of

principal elements

Alloys	elastic instability mechanism
TiHfZrNbTa	Elastic strain-induced amorphization
TiHfZrNb	Elastic strain-induced amorphization
TaHfZrNb	Elastic strain-induced amorphization
TiZrNb	Elastic strain-induced amorphization
HfZrNb	Elastic strain-induced amorphization
TiHfNb	Elastic strain-induced amorphization
TiNb	Crystalline phase transformation
ZrNb	Crystalline phase transformation
TiZr	Partial dislocations
Nb ¹¹	Crystalline phase transformation, twinning
INU	and dislocations



Supplementary Figure 1 | Loading-unloading during tension of a TiHfZrNb
sample. a, The initial TiHfZrNb sample; b, The TiHfZrNb sample is elastically
stretched to 7.3% without any inelastic relaxation; c, The TiHfZrNb sample recovers
its initial shape after complete unloading.







Supplementary Figure 2 | Another example of the amorphization in [110] tension-2 loaded TiHfZrNb sample. a, A crystalline HEA sample was loaded in tension around 3 4 [110]. **b**, The critical lattice with the elastic strain of 10% (determined by the (110) lattice spacing change) prior to the occurrence of amorphization. c, A segment of 5 amorphous structure (outlined by a pair of yellow dashed lines) formed in the area with 6 severe elastic deformation. d, The amorphous segment propagates as further tensile 7 8 load applies. The insets in a and d are corresponding FFT pattern, which show the 9 crystalline and amorphous nature of the sample before and after tensile test, respectively.



Supplementary Figure 3 | A nanoscale HEA sample was exposed to electron
irradiation for 30 min. No structural change can be detected (a) before and (b) after
irradiation. The crystal-amorphous interface was outlined by the yellow lines, and the
insets are corresponding FFT images. Insets in a and b are corresponding FFT pattern.







Supplementary Figure 4 | A TiHfZrNb HEA sample was stretched with electron beam switched off. a, The initial HEA lattice. b, A strain-induced amorphous segment (outlined by a pair of red dashed lines) was still produced when the beam was switched off. Insets are the corresponding FFT pattern, showing the crystalline and amorphous nature of the sample before and after tensile test, respectively.



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Supplementary Figure 5 | High-resolution TEM images viewed at different tilting angles. (a) $\alpha = -20^{\circ}$, (b) $\alpha = 0^{\circ}$ and (c) $\alpha = 20^{\circ}$ of a TiHfZrNb sample containing amorphous structure (outlined by the dashed red line) generated by elastic straininduced amorphization.

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Supplementary Figure 6 | Amorphous band in 90% rolled bulk TiHfZrNb sample.
a, Bright-field TEM image for the band-like structure in 90% rolled bulk TiHfZrNb
sample. b, The corresponding selected area diffraction pattern. c, High-resolution TEM
image shows the amorphous and crystalline bands. d, High-resolution TEM image
shows the interface of amorphous structure and crystal.



Supplementary Figure 7 | High density of dislocations in 30% rolled bulk
TiHfZrNb sample. a, Bright-field TEM image for the microstructure of 30% rolled
bulk TiHfZrNb sample. b, Corresponding selected area diffraction pattern. c, Highresolution image to reveal the dislocation cores.







a, Initial nanoscale ZrNb lattice; **b**, Elastically deformed lattice at a critical state; **c**,

- 7 ZrNb lattice containing FCC lattice.



quaternary alloy TaHfZrNb (a1, before tension, a2, after tension), ternary alloys
HfZrNb (b1, before tension, b2, after tension) and TiHfNb (c1, before tension, c2,
after tension), respectively.



Supplementary Figure 10 | Elastic instability in binary alloy samples is dominated by dislocations and crystalline phase transformation. a1-3, The elastic instability of TiZr sample with a hexagonal close packed (HCP) lattice is dominated by partial dislocations without elastic strain-induced amorphization. b1-4, A transformation from the BCC to HCP lattice was detected in the TiNb sample without elastic strain-induced amorphization. b3 shows the orientation relationship between BCC and the product HCP lattice.



Supplementary Figure 11 | Dislocations mediated elastic instability in nanoscale
quinary FCC-structured (a) FeCoNiCrCu and (b) FeCoNiCrMn. Insets in a are
corresponding FFT pattern, showing the crystalline nature of the sample before and
after tensile test. Inset in b is an enlarged view of the dashed square area.



2 Supplementary Figure 12 | Schematic image show the variation of Gibbs free 3 energy with temperature when low-temperature amorphization occurs in a crystal. It is remarkable that the crystal involved must have a higher entropy ($S = -(\partial G/\partial T)$, 4 5 corresponding to the slope of the Gibbs free energy curves) than the liquid phase (i.e., amorphous structure) at low temperature. The coordination number in liquids and 6 7 glasses, 11-12, is close to 12 in close-packed FCC crystals, but is significantly higher than 8 in non-close-packed BCC crystals. BCC crystals will generally have a higher 8 9 vibrational entropy than close-packed FCC crystals and amorphous structure, which favors the amorphization at low-temperature. 10





Supplementary Figure 13 | Energy storage through elastic deformation. a-c,
Atomic configurations of amorphous TiHfZrNb, undeformed crystalline TiHfZrNb and
loaded to a tensile strain of 10% in TiHfZrNb, respectively. d, The energy and stress of
TiHfZrNb lattice increases with elastic strain; the black line represents the energy of
the amorphous configuration of TiHfZrNb in a.



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2 Supplementary Figure 14 | Molecular dynamic simulations for the lattice evolution on (011) plane with tensile strain in nanoscale elemental Nb (a1-a4) and TaHfZrNb 3 HEA (b1-b4). Two samples have the same initial configuration (a1, b1). Dislocation-4 mediated elastic instability is found in the nanoscale elemental Nb after reaching the 5 6 elastic strain limit (a2). a3-a4 show the plastic deformation of Nb is dominated by 7 dislocation slip; the nanoscale Nb retains an ordered lattice even after fracture occurs. **b2** shows that several disordered regions emerge in TaHfZrNb after the elastic limit is 8 reached, which indicates that the elastic instability in TaHfZrNb is mediated by elastic 9 10 strain-induced amorphization. **b3-b4** show the disordered regions coarsened during further plastic deformation. c1 and c2 show the non-affine atomic displacements 11 mapping of Nb, corresponding to a2 and a3. d1 and d2 show the non-affine atomic 12 displacements mapping of TaHfZrNb, corresponding to b2 and b3. The observed 13 14 experimental scenarios are well reproduced in MD simulations, which show that the mechanisms underpinning the elastic instability in elemental Nb and the quaternary 15 TaHfZrNb are, respectively, dislocation slip and elastic strain-induced amorphization. 16 Additionally, non-affine atomic displacement mapping of Nb at strains exceeding the 17 elastic strain limit shows that the atomic displacements are focused on the {112} slip 18 19 plane, which corresponds to the glide of dislocations. However, the non-affine atomic

displacements in the quaternary TaHfZrNb are extensively distributed in an irregular 1 2 manner at strains above the elastic strain limit of $\sim 10\%$, which activates the elastic 3 strain-induced amorphization phenomenon. Atoms in blue represent atoms in a BCC structure; those in silver white represent atoms in a disordered structure. Atoms in other 4 colors represent the value of non-affine displacement scaling with the scale bar in (c1, 5 c2, d1 and d2). Both MD samples possess a circular cross-section. Affine displacement 6 is a geometric transformation that linearly alters the position of atoms in space, 7 8 reflecting the uniform movement of atoms along the slip plane facilitated by dislocation 9 slipping. Conversely, non-affine displacement captures the disordered movement of atoms during amorphization. Additionally, our research focuses on the middle position 10 of the sample, which is characterized by stress concentration and exhibits a circular 11 12 cross-section in both experimental and simulated conditions. This midpoint is far away from the specimen ends where external loads were applied. As a result, we can 13 confidently disregard any deviation in stress distribution associated with variations in 14 the shape of the specimen ends, as illustrated by St. Venant's principle⁷. 15



3 Supplementary Figure 15 | Atomic-scale element distribution analysis for binary **TiZrNb alloys**. **a**, HAADF-STEM image along the [111] zone axis, and corresponding 4 atomically resolved EDS maps for individual elements of Ti and Nb. b1-2, Zoomed-in 5 images captured from the local regions in **a**, compared with the various local chemical 6 7 groups in ternary TiZrNb alloy, there are just two kinds of local groups in TiNb alloy, i.e., the Ti- and Nb-rich local groups. c, Line profiles representing the distribution of 8 individual elements in $(1\overline{10})$ planes projected along the [111] direction. Compared 9 with TiZrNb alloy, the variation of atomic fraction of individual elements is smaller. d, 10 11 Plots of the pair correlation function of individual elements of TiNb alloy, which possess low and broad peaks for each element, indicating the elements distribution in 12 TiNb alloy is random. 13





2 Supplementary Figure 16 | EBSD orientation map (the leftmost column), EBSD phase map

3 (second column from left) and EDS maps of each constituent element (the other images with

- 4 element symbol on the upper right corner) for the samples used in this study.
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Supplementary Figure 17 | Cross-section of the nanoscale HEA sample observed by tilting the nanoscale sample along the α direction from -25° to +25°. Cross-section images of the nanoscale sample tilted at angles of (a) -25°, (b) 0° and (c) +25°. The diameter of the nanoscale sample changes little, which indicates that the cross section of the nanoscale HEA sample is nearly circular.

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Supplementary Figure 18 | Preparation of the sample. a, A schematic illustration of
 in situ welding; b, A HEA sample prepared from HEA nano-tips by an electric pulse

- 4 with duration time of 1 ms and voltage range of 0-2V.

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